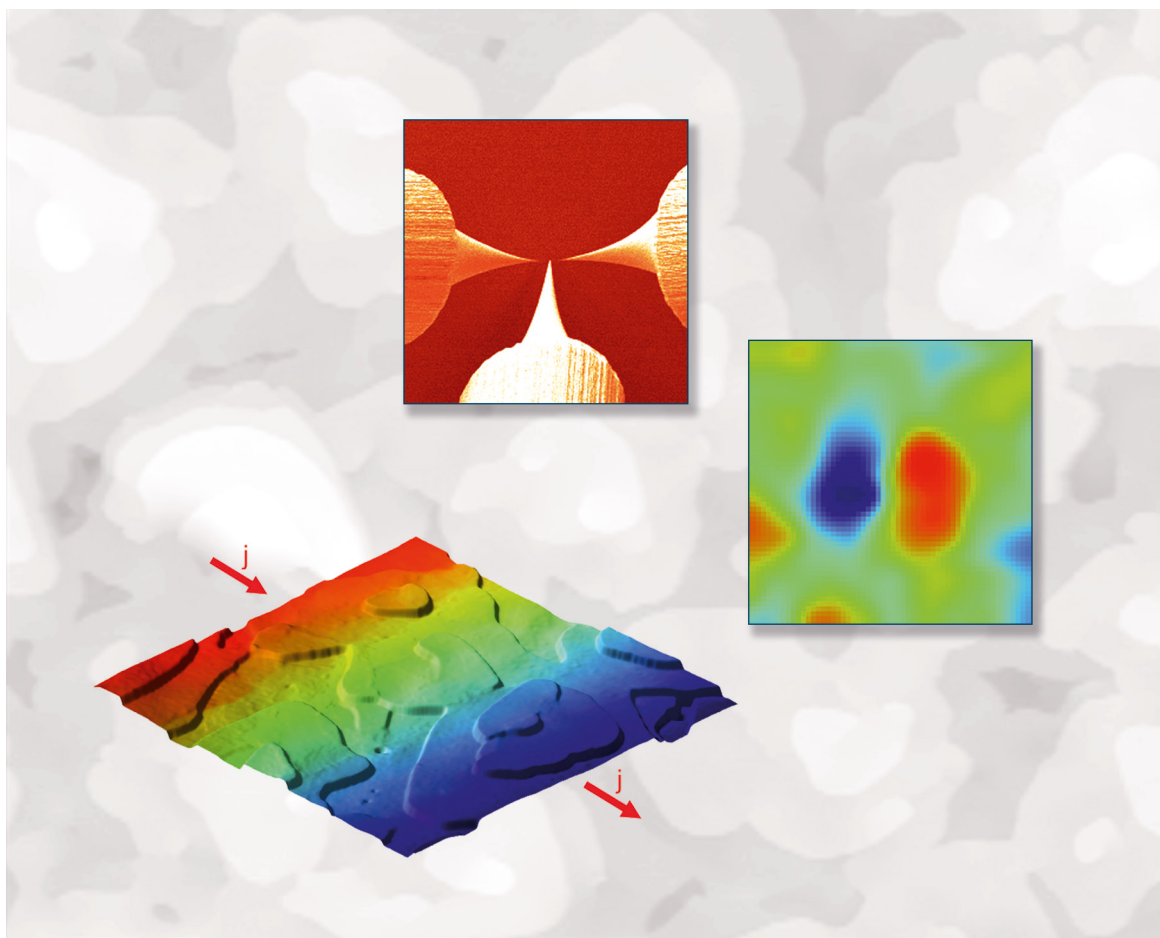




Scanning tunneling potentiometry at nanoscale defects in thin films

Felix Lüpke

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